

TOSHIBA Field Effect Transistor with Built-in Schottky Barrier Diode  
Silicon N-Channel MOS Type (U-MOS V-H)

# TPC8A04-H

High Efficiency DC-DC Converter Applications

Notebook PC Applications

Portable Equipment Applications

- Built-in schottky barrier diode  
Low forward voltage:  $V_{DSF} = -0.6 \text{ V (max)}$
- High-speed switching
- Small gate charge:  $Q_{SW} = 13 \text{ nC (typ.)}$
- Low drain-source ON-resistance:  $R_{DS(ON)} = 2.6 \text{ m}\Omega \text{ (typ.)}$
- High forward transfer admittance:  $|Y_{fs}| = 62 \text{ S (typ.)}$
- Low leakage current:  $I_{DSS} = 100 \text{ }\mu\text{A (max)}$  ( $V_{DS} = 30 \text{ V}$ )
- Enhancement mode:  $V_{th} = 1.3 \text{ to } 2.3 \text{ V}$  ( $V_{DS} = 10 \text{ V}$ ,  $I_D = 1 \text{ mA}$ )

## Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

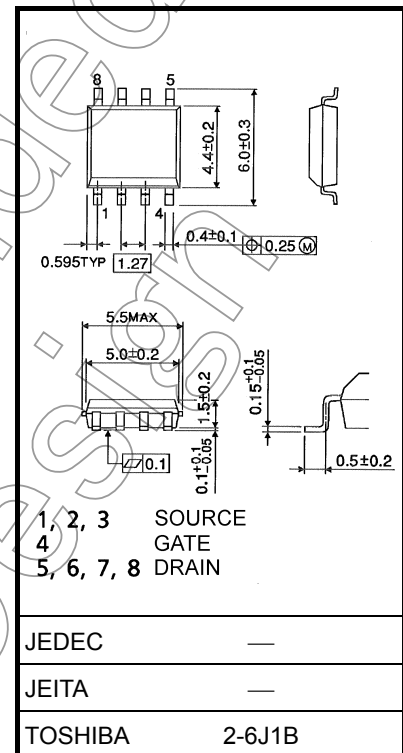
Characteristic		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	30	V
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )		$V_{DGR}$	30	V
Gate-source voltage		$V_{GSS}$	$\pm 20$	V
Drain current	DC (Note 1)	$I_D$	18	A
	Pulsed (Note 1)	$I_{DP}$	72	
Drain power dissipation ( $t = 10 \text{ s}$ ) (Note 2a)		$P_D$	1.9	W
Drain power dissipation ( $t = 10 \text{ s}$ ) (Note 2b)		$P_D$	1.0	W
Single-pulse avalanche energy (Note 3)		$E_{AS}$	211	mJ
Avalanche current		$I_{AR}$	18	A
Repetitive avalanche energy ( $T_c = 25^\circ\text{C}$ ) (Note 4)		$E_{AR}$	0.082	mJ
Channel temperature		$T_{ch}$	150	$^\circ\text{C}$
Storage temperature range		$T_{stg}$	-55 to 150	$^\circ\text{C}$

Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

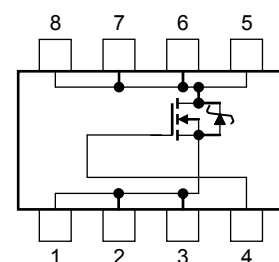
This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



Weight: 0.085g (typ.)

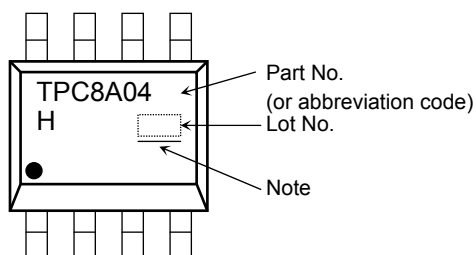
## Circuit Configuration



## Thermal Characteristics

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	$R_{th(ch-a)}$	65.8	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	$R_{th(ch-a)}$	125	°C/W

## Marking (Note 5)



Note : A line under a Lot No. identifies the indication of product Labels  
[[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

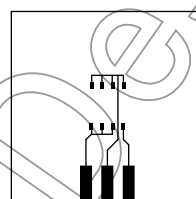
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)



(a)



(b)

Note 3:  $V_{DD} = 24\text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 500\text{ }\mu\text{H}$ ,  $R_G = 25\text{ }\Omega$ ,  $I_{AR} = 18\text{ A}$

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: \* Weekly code: (Three digits)



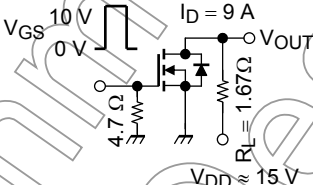
Week of manufacture

(01 for the first week of the year, continuing up to 52 or 53)

Year of manufacture

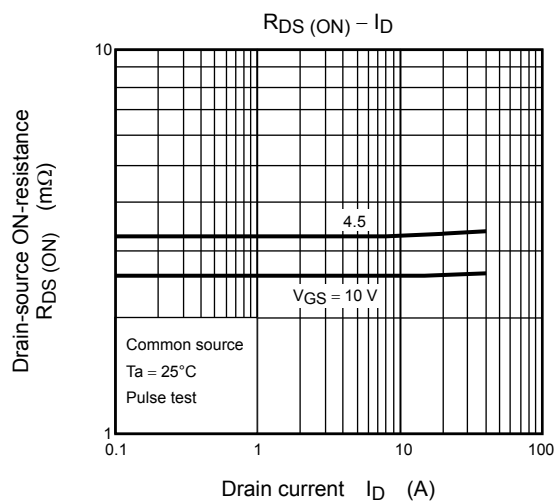
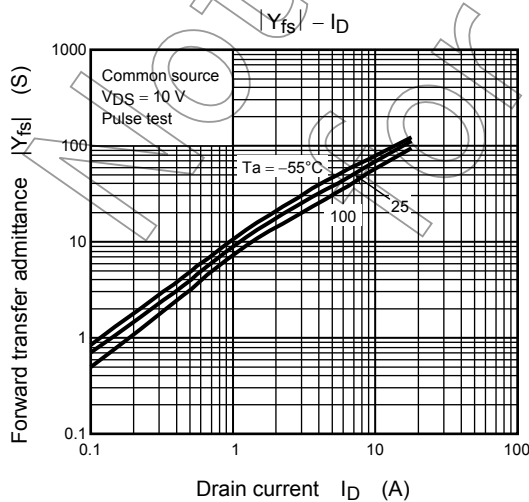
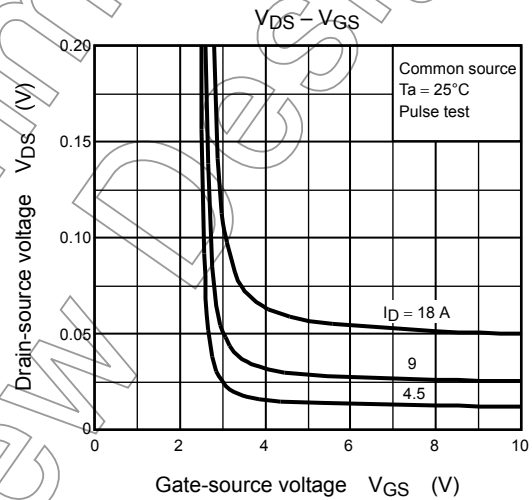
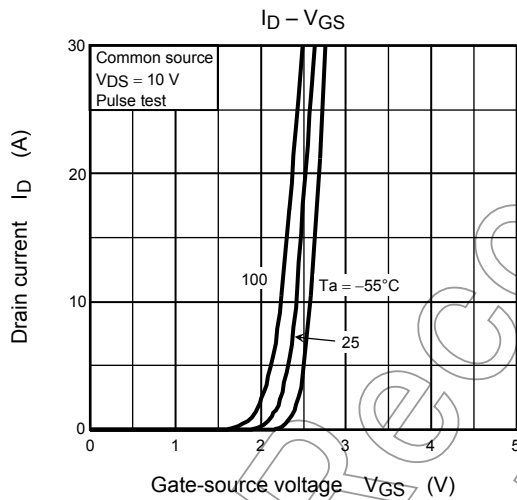
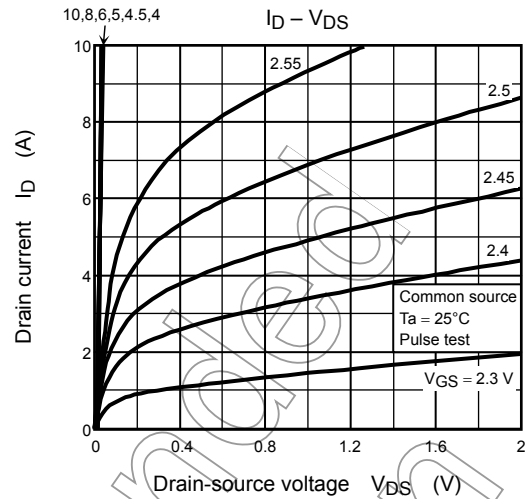
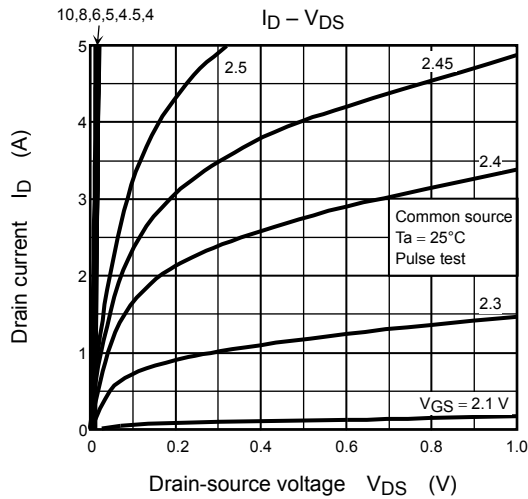
(The last digit of the year)

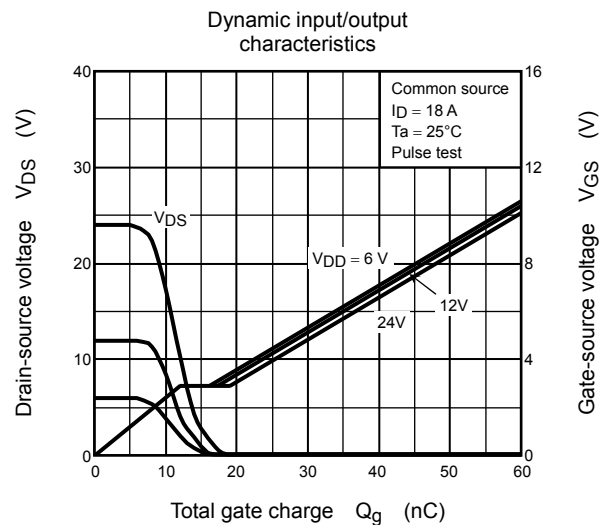
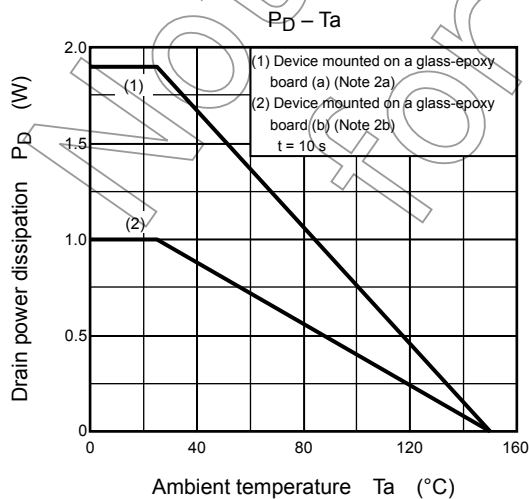
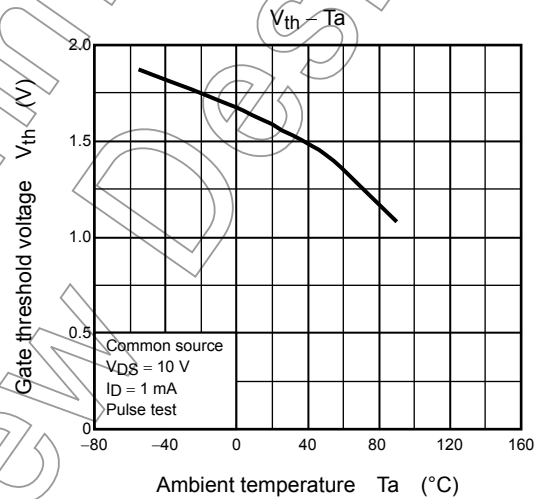
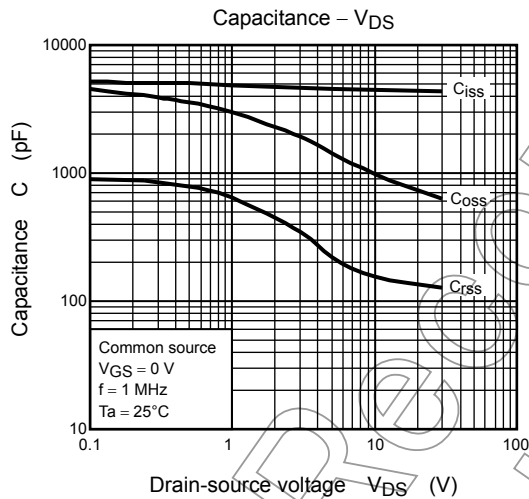
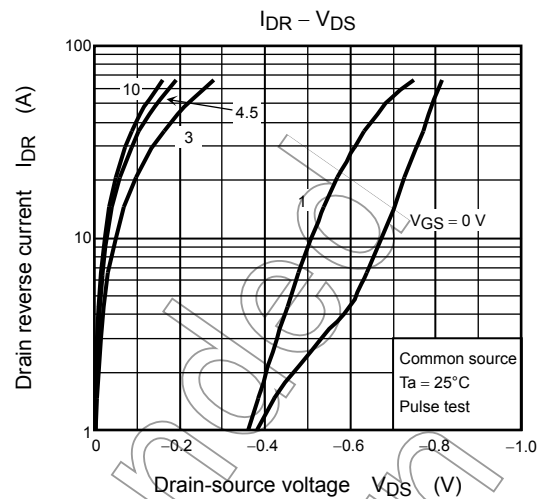
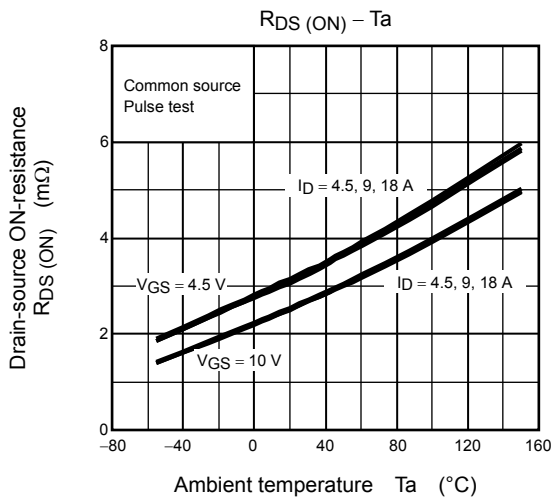
## Electrical Characteristics (Ta = 25°C)

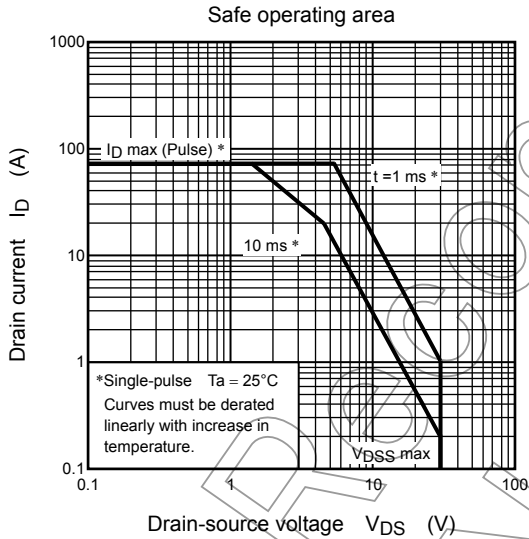
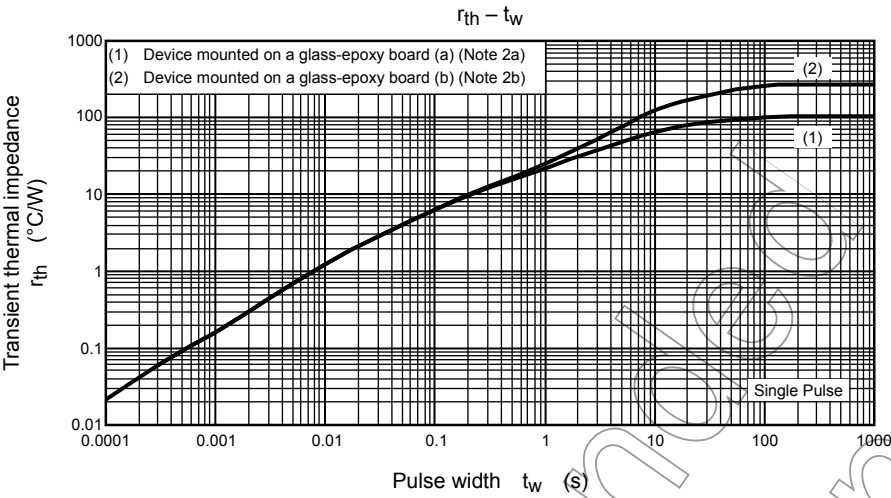
Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V	—	—	±100	nA
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V	—	—	100	μA
Drain-source breakdown voltage		V <sub>(BR)</sub> DSS	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	30	—	—	V
		V <sub>(BR)</sub> DSX	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = −20 V	15	—	—	
Gate threshold voltage		V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	1.3	—	2.3	V
Drain-source ON-resistance		R <sub>DS</sub> (ON)	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 9 A	—	3.2	4.5	mΩ
			V <sub>GS</sub> = 10 V, I <sub>D</sub> = 9 A	—	2.6	3.6	
Forward transfer admittance		Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 9 A	31	62	—	S
Input capacitance		C <sub>iss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	—	4400	5700	pF
Reverse transfer capacitance		C <sub>rss</sub>		—	180	270	
Output capacitance		C <sub>oss</sub>		—	990	—	
Gate resistance		r <sub>g</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 5 MHz	—	1.0	1.5	Ω
Switching time	Rise time	t <sub>r</sub>	 V <sub>GS</sub> = 10 V, 0 V, I <sub>D</sub> = 9 A, V <sub>OUT</sub> , 4.7 Ω, 1.67 Ω, V <sub>DD</sub> ≈ 15 V, R <sub>L</sub> = 1.67 Ω, Duty ≤ 1%, t <sub>w</sub> = 10 μs	—	4.5	—	ns
	Turn-on time	t <sub>on</sub>		—	13.2	—	
	Fall time	t <sub>f</sub>		—	7.7	—	
	Turn-off time	t <sub>off</sub>		—	54	—	
Total gate charge (gate-source plus gate-drain)		Q <sub>g</sub>	V <sub>DD</sub> ≈ 24 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 18 A	—	56	—	nC
			V <sub>DD</sub> ≈ 24 V, V <sub>GS</sub> = 5 V, I <sub>D</sub> = 18 A	—	29	—	
Gate-source charge 1		Q <sub>gs1</sub>	V <sub>DD</sub> ≈ 24 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 18 A	—	12	—	
Gate-drain (“Miller”) charge		Q <sub>gd</sub>		—	7.0	—	
Gate switch charge		Q <sub>sw</sub>		—	13	—	

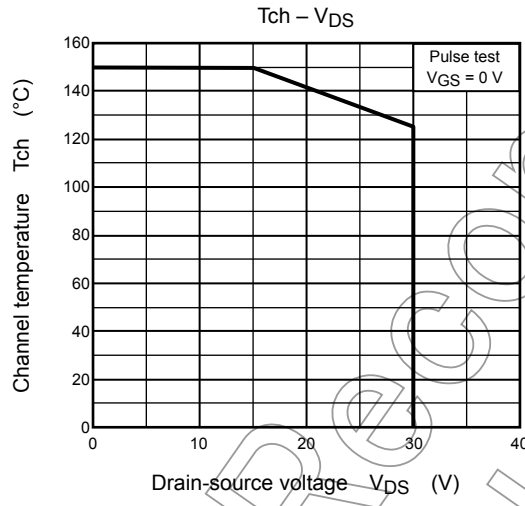
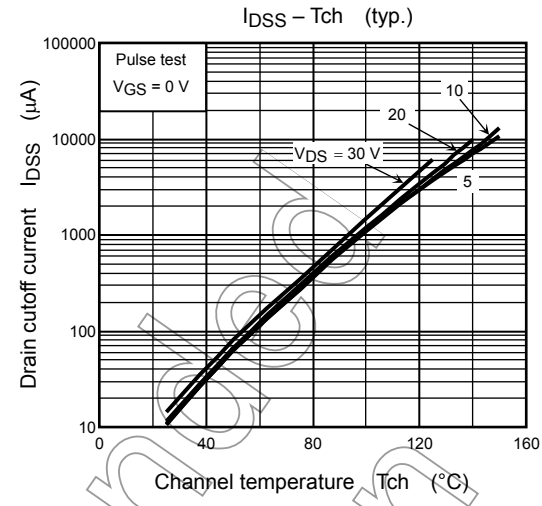
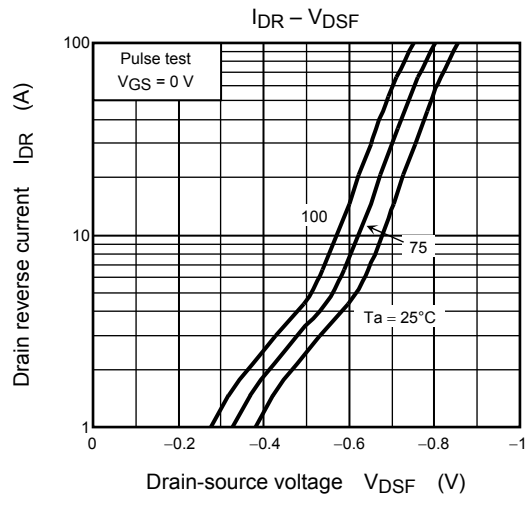
## Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	$I_{DRP}$	—	—	—	72	A
Forward voltage (diode)		$V_{DSF}$	$I_{DR} = 1 \text{ A}, V_{GS} = 0 \text{ V}$	—	-0.4	-0.6	V
			$I_{DR} = 18 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	-1.2	V









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